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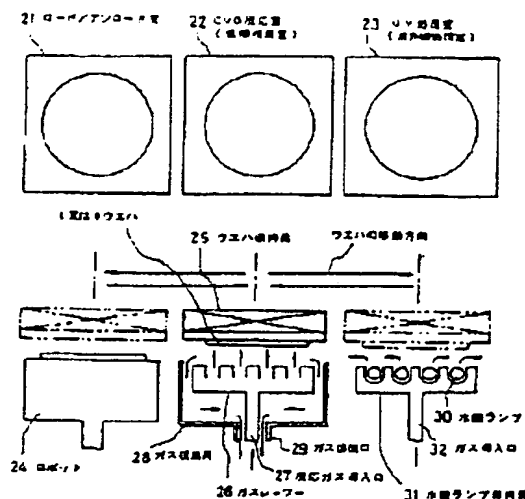
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APPLICANT : HANDOTAI PROCESS
KENKYUSHO:KK;

INVENTOR : NISHIMOTO HIROKO;

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TITLE : SEMICONDUCTOR MANUFACTURING
APPARATUS AND MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To improve the film quality of an insulating film by a method wherein the insulating film is formed on a body, to be formed, by a vapor growth (CVD) method and, after that, an ultraviolet irradiation treatment is executed to the surface of the insulating film.

CONSTITUTION: A loading/unloading chamber 21, a CVD reaction chamber (a vapor growth chamber) 22 and a UV treatment chamber (an ultraviolet treatment chamber) 23 are connected in this arrangement; a wafer 1 or 9 is moved to the loading/unloading chamber 21 by using a robot 24 or the like; and a series of treatments such as a vapor growth treatment and an ultraviolet irradiation treatment can be executed continuously. An insulating film is formed on a body, to be formed, by the vapor growth treatment. After that, while it is being heated, the ultraviolet irradiation treatment is executed to the surface of the insulating film. Thereby, it is possible to improve the film quality of the insulating film by the CVD method by which a film can be formed at a low temperature, and it is possible to maintain a mass productivity.

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